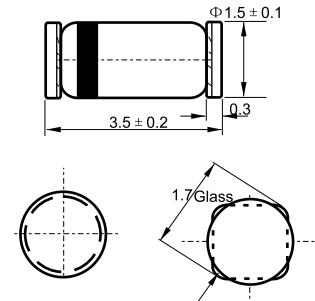




### MINI MELF



Dimension in millimeters

### Features

- ✧ Fast Switching Speed
- ✧ Surface Mount Package Ideally Suited for Automatic Insertion
- ✧ General Purpose Rectification
- ✧ Silicon Epitaxial Planar Construction

### Mechanical Data

- ✧ Case: MiniMELF
- ✧ Polarity: Cathode Band
- ✧ Marking: Cathode Band Only
- ✧ Weight: 0.12 grams (approx.)

### Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

#### Maximum Ratings

Characteristic	Symbol	BAS32L	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	110	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current (Note 1)	$I_{FM}$	500	mA
Average Rectified Output Current (Note 1)	$I_O$	150	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0s @ t = 1.0μs	$I_{FSM}$	1.0 2.0	A
Power Dissipation (Note 1) Derate Above 25°C	$P_d$	500 1.68	mW mW/°C
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{θJA}$	300	K/W
Operating and Storage Temperature Range	$T_j, T_{STG}$	-65 to +175	°C

#### Electrical Characteristics

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage	$V_{FM}$	0.62 —	0.72 1.0	V	$I_F = 5.0mA$ $I_F = 100mA$
Maximum Peak Reverse Current	$I_{RM}$	—	5.0 50 30 25	μA μA μA nA	$V_R = 75V$ $V_R = 70V, T_j = 150°C$ $V_R = 20V, T_j = 150°C$ $V_R = 20V$
Capacitance	$C_j$	—	4.0	pF	$V_R = 0, f = 1.0MHz$
Reverse Recovery Time	$t_{rr}$	—	4.0	ns	$I_F = 10mA$ to $I_R = 1.0mA$ $V_R = 6.0V, R_L = 100Ω$

Notes: 1. Valid provided that device terminals are kept at ambient temperature.

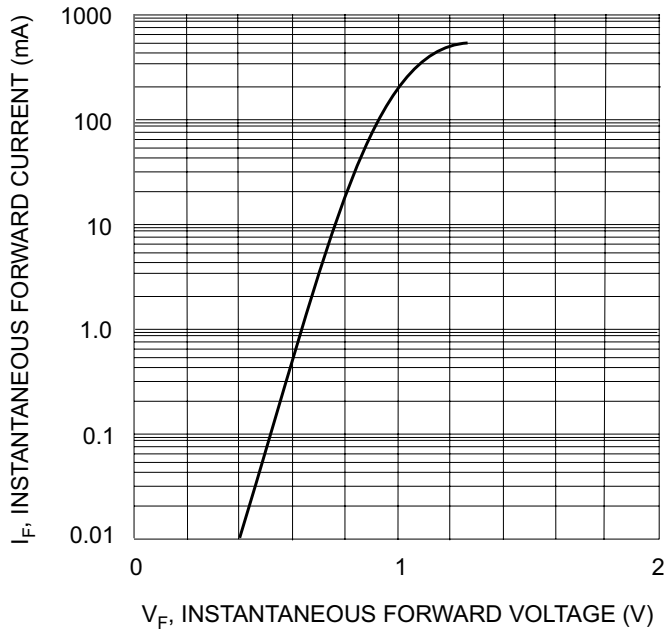


Fig. 1 Forward Characteristics

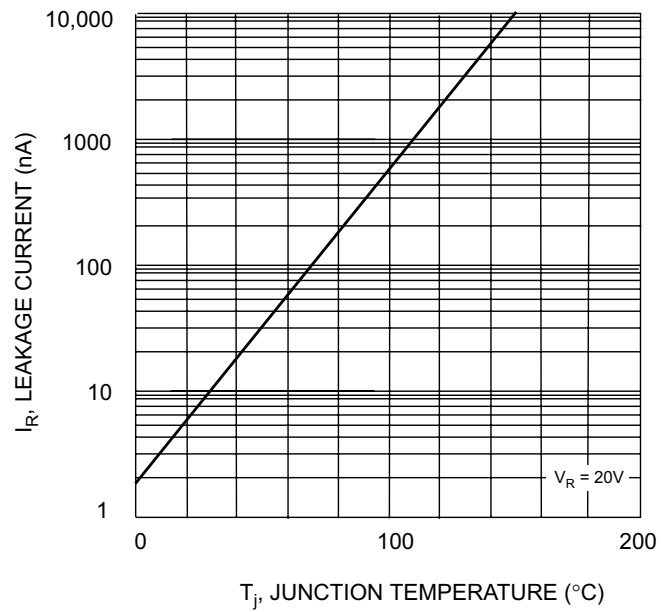


Fig. 2, Leakage Current vs Junction Temperature